



ELECTRONICS, INC.  
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## NTE582-4, NTE582-6 & NTE582-10 Fast Recovery Silicon Diode, 2A DO-15 Type Package

**Features:**

- Diffused Junction
- Low Forward Voltage Drop
- High Current Capability
- High Reliability
- High Surge Current Capability

**Maximum Ratings and Electrical Characteristics:** ( $T_A = +25^\circ\text{C}$  unless otherwise specified. Single phase, half wave, 60Hz, resistive or inductive load. For capacitive load, derate current by 20%.)

Peak Repetitive Reverse Voltage, $V_{RRM}$	
NTE582-4 .....	400V
NTE582-6 .....	600V
NTE582-10 .....	1000V
Working Peak Reverse Voltage, $V_{RWM}$	
NTE582-4 .....	400V
NTE582-6 .....	600V
NTE582-10 .....	1000V
DC Blocking Voltage, $V_R$	
NTE582-4 .....	400V
NTE582-6 .....	600V
NTE582-10 .....	1000V
RMS Reverse Voltage, $V_{R(RMS)}$	
NTE582-4 .....	280V
NTE582-6 .....	420V
NTE582-10 .....	700V
Average Forward Rectified Current ( $T_A = +55^\circ\text{C}$ , Note 1), $I_O$ .....	
2A	
Non-Repetitive Peak Forward Surge Current, $I_{FSM}$	
(8.3ms Single half Sine-Wave Superimposed on Rated Load) .....	
60A	
Forward Voltage ( $I_F = 2A$ ), $V_{FM}$ .....	
1.2V	
Peak Reverse Current (At rated DC Blocking Voltage), $I_{RM}$	
$T_J = +25^\circ\text{C}$ .....	5 $\mu\text{A}$
$T_J = +100^\circ\text{C}$ .....	100 $\mu\text{A}$
Reverse Recovery Time (Note 2), $t_{rr}$	
NTE582-4 .....	150ns
NTE582-6 .....	250ns
NTE582-10 .....	500ns
Typical Junction Capacitance (Note 3), $C_J$ .....	
30pF	

Note 1. Leads maintained at ambient temperature at a distance of 9.5mm from the case.

Note 2. Measured at  $I_F = 500\text{mA}$ ,  $I_R = 1A$ ,  $I_{RR} = 250\text{mA}$ .

Note 3. Measured at 1MHz an Applied Reverse Voltage of 4.0VDC.



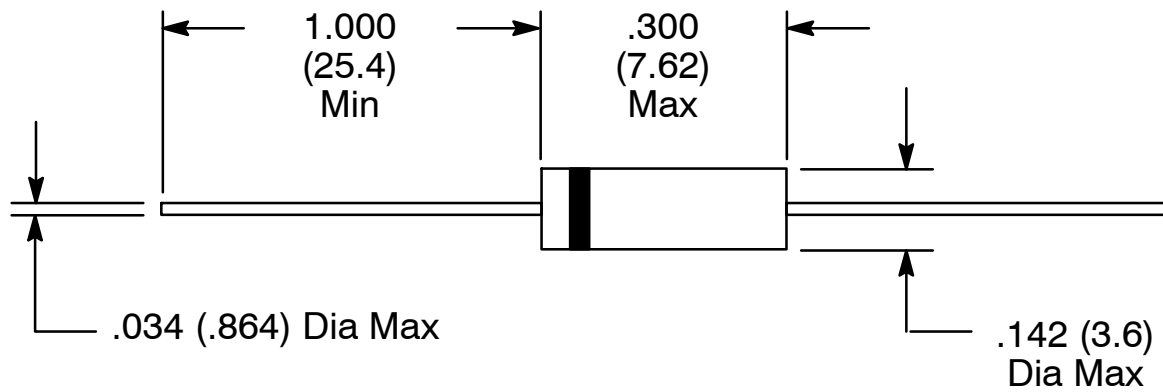
**Maximum Ratings and Electrical Characteristics (Cont'd):** ( $T_A = +25^\circ\text{C}$  unless otherwise specified. Single phase, half wave, 60Hz, resistive or inductive load. For capacitive load, derate current by 20%.)

Thermal Resistance, Junction-to-Ambient (Note 1), $R_{thJA}$ .....	40°C/W
Thermal Resistance, Junction-to-Lead (Note 1), $R_{thJL}$ .....	20°C/W
Operating Junction Temperature Range, $T_J$ .....	-65° to +125°C
Storage Temperature Range, $T_{stg}$ .....	-65° to +150°C

Note 1. Leads maintained at ambient temperature at a distance of 9.5mm from the case.

Note 2. Measured at  $I_F = 500\text{mA}$ ,  $I_R = 1\text{A}$ ,  $I_{RR} = 250\text{mA}$ .

Note 3. Measured at 1MHz an Applied Reverse Voltage of 4.0VDC.



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